

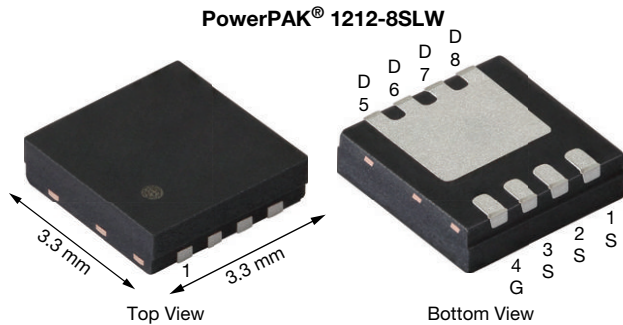
Automotive N-Channel 40 V (D-S) 175 °C MOSFET



RoHS
COMPLIANT
HALOGEN
FREE

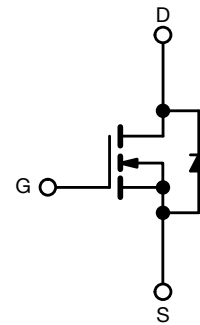
FEATURES

- TrenchFET® Gen IV power MOSFET
- AEC-Q101 qualified
- 100 % R_g and UIS tested
- Wettable flank terminals
- Low thermal resistance with 0.75 mm profile
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



Marking code: Q042

PRODUCT SUMMARY	
V _{DS} (V)	40
R _{DS(on)} (Ω) at V _{GS} = 10 V	0.00253
I _D (A) ^e	152
Configuration	Single



N-Channel MOSFET

ORDERING INFORMATION	
Package	PowerPAK® 1212-8SLW
Lead (Pb)-free and halogen-free	SQS140ENW (for detailed order number please see www.vishay.com/doc?79771)

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT
Drain-source voltage	V _{DS}	40	V
Gate-source voltage	V _{GS}	± 20	
Continuous drain current ^e	I _D	T _C = 25 °C	152
		T _C = 125 °C	87
Continuous source current (diode conduction) ^e	I _S	108	A
Pulsed drain current ^{a, e}	I _{DM}	350	
Single pulse avalanche current	I _{AS}	31.5	mJ
Single pulse avalanche energy	E _{AS}	49.6	
Maximum power dissipation ^{a, e}	P _D	T _C = 25 °C	119
		T _C = 125 °C	39
Operating junction and storage temperature range	T _J , T _{stg}	-55 to +175	°C
Soldering recommendations (peak temperature) ^c		260	

THERMAL RESISTANCE RATINGS			
PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-ambient	R _{thJA}	54	°C/W
Junction-to-case (drain) ^d	R _{thJC}	1.26	

Notes

- Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %
- When mounted on 1" square PCB (FR4 material)
- See solder profile (www.vishay.com/doc?73257). A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- As per JESD51-14
- Values based on R_{thJC} and T_C of 25 °C. Actual values achievable will be dependent on the thermal characteristics of the complete system



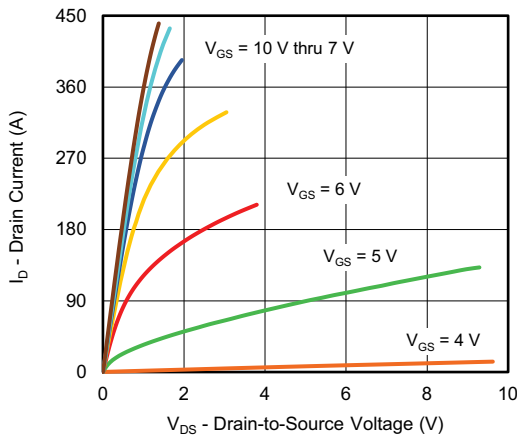
SPECIFICATIONS ($T_C = 25\text{ }^\circ\text{C}$, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V_{DS}	$V_{GS} = 0, I_D = 250\text{ }\mu\text{A}$		40	-	-	V
Gate-source threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$		2.5	3.0	3.5	
Gate-source leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$		-	-	± 100	nA
Zero gate voltage drain current	I_{DSS}	$V_{GS} = 0\text{ V}$	$V_{DS} = 40\text{ V}$	-	-	1	μA
		$V_{GS} = 0\text{ V}$	$V_{DS} = 40\text{ V}, T_J = 125\text{ }^\circ\text{C}$	-	-	50	
		$V_{GS} = 0\text{ V}$	$V_{DS} = 40\text{ V}, T_J = 175\text{ }^\circ\text{C}$	-	-	150	
On-state drain current ^a	$I_{D(on)}$	$V_{GS} = 10\text{ V}$	$V_{DS} \geq 5\text{ V}$	20	-	-	A
Drain-source on-state resistance ^a	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$	$I_D = 10\text{ A}$	-	0.0021	0.00253	Ω
		$V_{GS} = 10\text{ V}$	$I_D = 10\text{ A}, T_J = 125\text{ }^\circ\text{C}$	-	-	0.0038	
		$V_{GS} = 10\text{ V}$	$I_D = 10\text{ A}, T_J = 175\text{ }^\circ\text{C}$	-	-	0.0043	
Forward transconductance ^b	g_{fs}	$V_{DS} = 15\text{ V}, I_D = 10\text{ A}$		-	55	-	S
Dynamic ^b							
Input capacitance	C_{iss}	$V_{GS} = 0\text{ V}$	$V_{DS} = 25\text{ V}, f = 1\text{ MHz}$	-	2222	3111	pF
Output capacitance	C_{oss}			-	923	1295	
Reverse transfer capacitance	C_{rss}			-	37	52	
Total gate charge ^c	Q_g	$V_{GS} = 10\text{ V}$	$V_{DS} = 20\text{ V}, I_D = 5\text{ A}$	-	38	57	nC
Gate-source charge ^c	Q_{gs}			-	11	-	
Gate-drain charge ^c	Q_{gd}			-	8	-	
Gate resistance	R_g	f = 1 MHz		0.5	1.1	1.7	Ω
Turn-on delay time ^c	$t_{d(on)}$	$V_{DD} = 20\text{ V}, R_L = 1.33\text{ }\Omega$ $I_D \cong 15\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\text{ }\Omega$		-	13	20	ns
Rise time ^c	t_r			-	5	9	
Turn-off delay time ^c	$t_{d(off)}$			-	22	33	
Fall time ^c	t_f			-	8	12	
Source-Drain Diode Ratings and Characteristic ^b							
Pulsed current ^a	I_{SM}			-	-	350	A
Forward voltage	V_{SD}	$I_F = 10\text{ A}, V_{GS} = 0\text{ V}$		-	0.82	1.1	V
Body diode reverse recovery time	t_{rr}	$I_F = 5\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		-	38	78	ns
Body diode reverse recovery charge	Q_{rr}			-	34	70	nC
Reverse recovery fall time	t_a			-	19	-	ns
Reverse recovery rise time	t_b			-	20	-	
Body diode peak reverse recovery current	$I_{RM(REC)}$			-	-1.6	-3.2	A

Notes

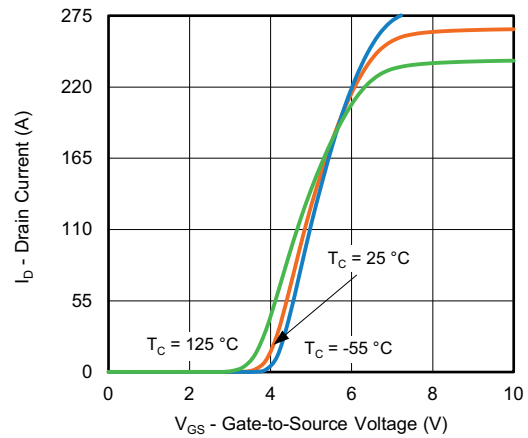
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

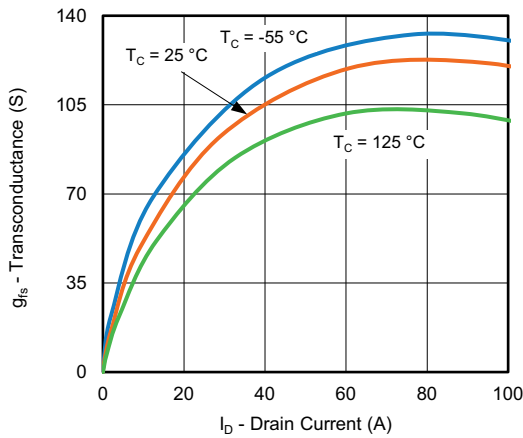
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



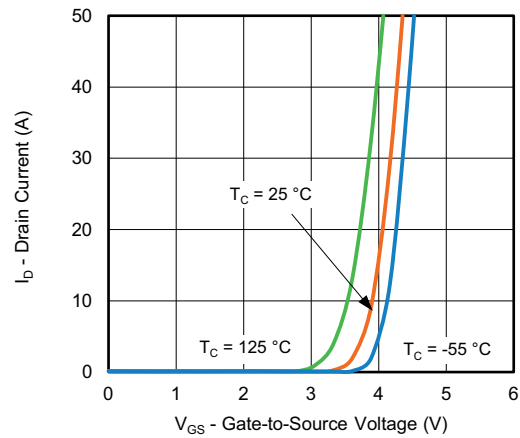
Output Characteristics



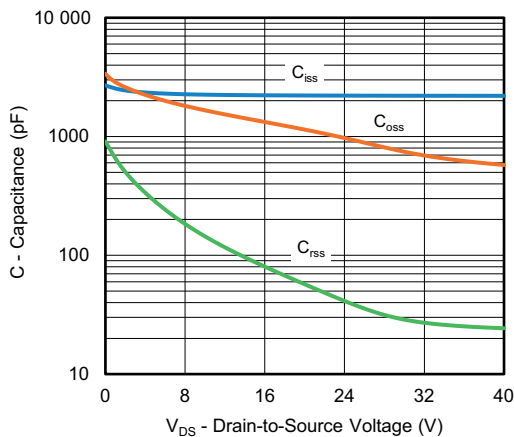
Transfer Characteristics



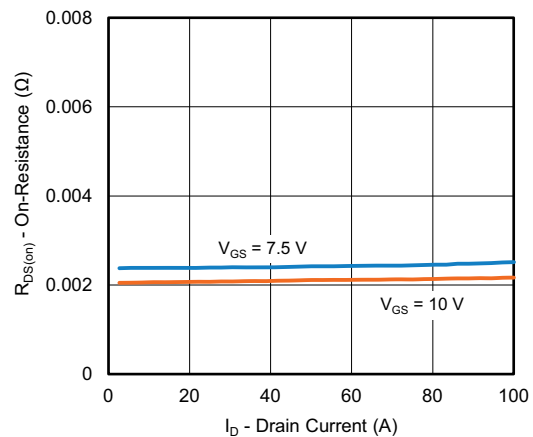
Transconductance



Transfer Characteristics

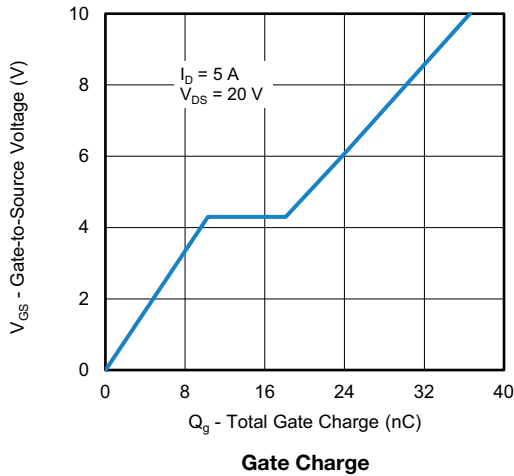


Capacitance

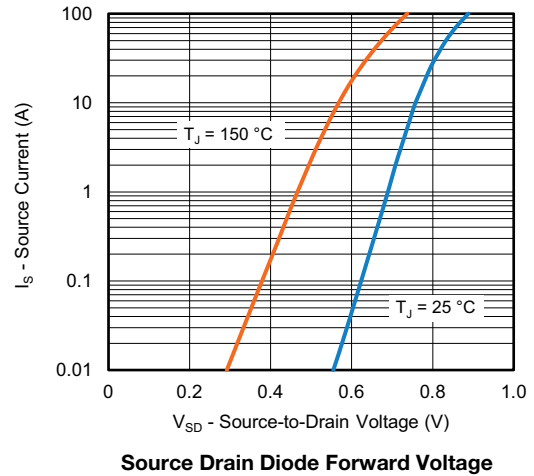


On-Resistance vs. Drain Current

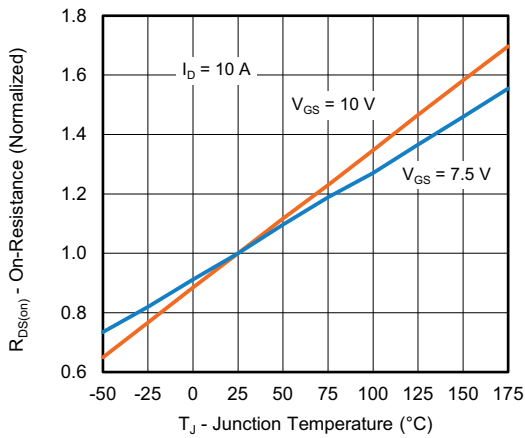
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



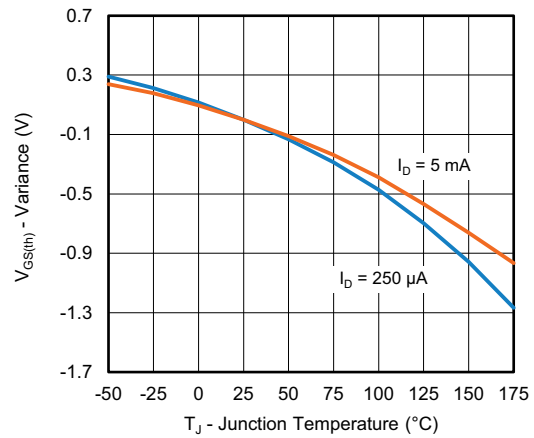
Gate Charge



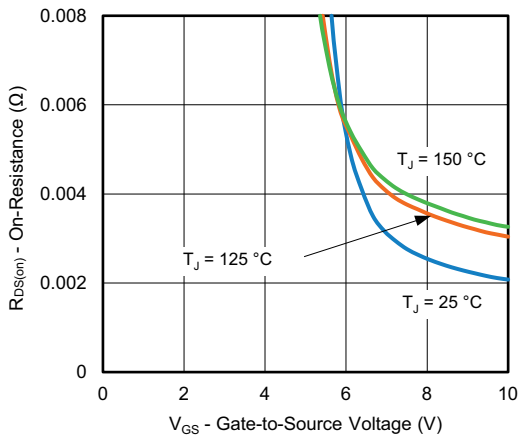
Source Drain Diode Forward Voltage



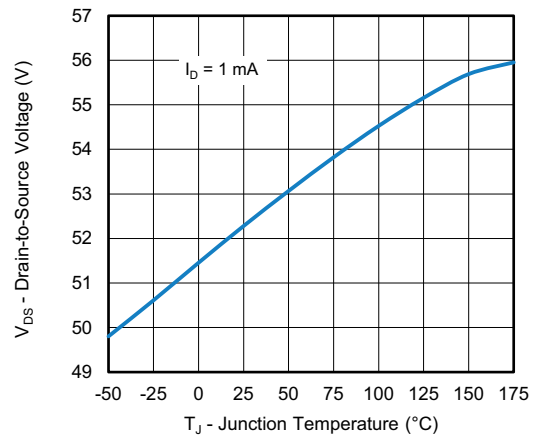
On-Resistance vs. Junction Temperature



Threshold Voltage



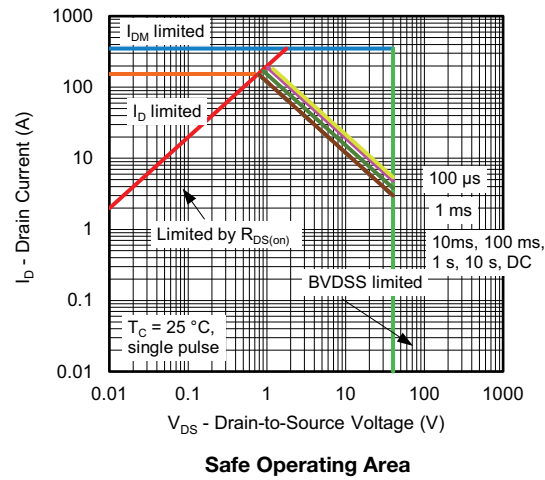
On-Resistance vs. Gate-to-Source Voltage



Drain Source Breakdown vs. Junction Temperature



THERMAL RATINGS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)

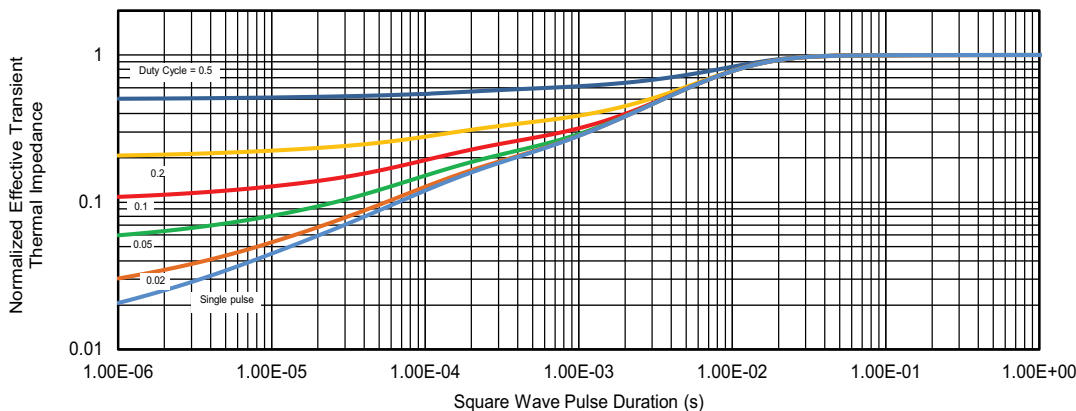


Note

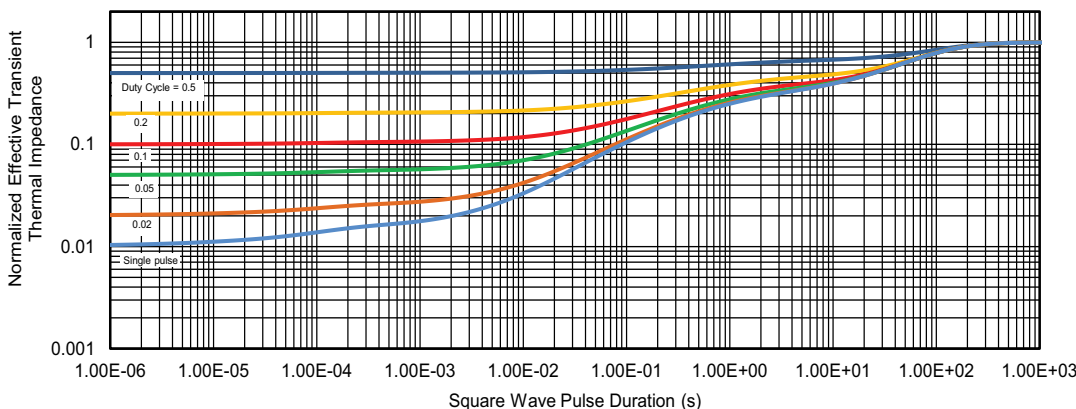
- a. $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified



THERMAL RATINGS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case



Normalized Thermal Transient Impedance, Junction-to-Ambient

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient ($25\text{ }^\circ\text{C}$)
 - Normalized Transient Thermal Impedance Junction-to-Case ($25\text{ }^\circ\text{C}$)
 are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

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RECOMMENDED MINIMUM PADS FOR PowerPAK® 1212-8 Single



Recommended Minimum Pads
Dimensions in Inches/(mm)

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